

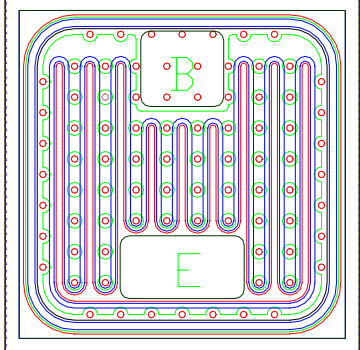
A1020 Silicon PNP Epitaxial Transistor

Description: The A1020 is designed for use in power amplifier applications and power switching applications

Features: ●Low collector saturation voltage

●Complementary to C2328

Chip Appearance

	Chip Size		760um × 760um
	Chip Thickness		210 ± 20um
	Bonding Pad Size	Base	160 × 170um
		Emitter	130 × 260um
	Front Metal		Al
	Backside Metal		Au
	Scribe line width		60um
Wafer Size		6 inch	

Electrical Characteristics(Ta=25°C)

Characteristic	Symbol	Test Condition	Min	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=-35V, I_E=0$		-0.1	uA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=-5V, I_C=0$		-0.1	uA
Collector-Base Breakdown Voltage	BV_{CBO}	$I_C=-0.1mA$	-40		V
Collector-Emitter Breakdown Voltage	BV_{CEO}	$I_C=-10mA$	-30		V
Emitter-Base Breakdown Voltage	BV_{EBO}	$I_E=-0.1mA$	-5.0		V
DC Current Gain	h_{FE}	$V_{CE}=-2V, I_C=-0.5A$	80	400	
Collector Saturation Voltage	$V_{CE(sat)}$	$I_C=-1A, I_B=-50mA$		-0.5	V